

Way Foong Lim

List of Publications by Year in descending order

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times ranked

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citing authors

#	ARTICLE	IF	CITATIONS
1	Exploratory studies on wet oxidation grown ternary hafnium tantalum oxide for <sc>metal-oxide semiconductor</sc> application. International Journal of Energy Research, 2022, 46, 4699-4711.	4.5	2
2	Synergetic effects of monoethanolamine (MEA) and post-deposition calcination on biosynthesized CeO ₂ nanostructures spin-coated on silicon substrate. Materials Chemistry and Physics, 2022, 278, 125656.	4.0	1
3	Effects of oxidation time on the formation of nanosized cerium oxide film from direct current sputtered cerium. Emergent Materials, 2022, 5, 41-49.	5.7	0
4	Analysis using a two-layer model of the transport properties of InGaN epilayers grown on GaN template substrate. Materials Science in Semiconductor Processing, 2022, 144, 106614.	4.0	3
5	Effect of etching time onto structural, morphological, and optical characteristics of quaternary AlInGaN films on Si substrate. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2021, 263, 114911.	3.5	1
6	Comparative study of oxidizing ambient infused with varying nitrogen flow rates for fabrication of ternary nitrided AlZrO based MOS capacitor. International Journal of Energy Research, 2021, 45, 3838-3851.	4.5	3
7	Formation of cerium oxide film via post-sputter oxidation of cerium in nitrogen/oxygen/nitrogen ambient. Journal of Alloys and Compounds, 2021, 851, 156786.	5.5	7
8	Tailoring In ₂ Ga ₂ ZnO ₇ thin film properties by annealing time effect. Materials Chemistry and Physics, 2021, 262, 124281.	4.0	1
9	Comparative studies of <sc>metal-organic</sc> decomposed <sc> Ga _{xyz} </sc> and <sc> CeO ₂ </sc> based functional <sc>MOS</sc> capacitor. International Journal of Energy Research, 2021, 45, 18257-18261.	4.5	3
10	Effects of V/III ratio of InGaN quantum well at high growth temperature for near ultraviolet light emitting diodes. Microelectronics International, 2021, 38, 119-126.	0.6	3
11	The role of growth temperature on the indium incorporation process for the MOCVD growth of InGaN/GaN heterostructures. Microelectronics International, 2021, 38, 105-112.	0.6	1
12	Investigation on structural, morphological, optical, and current-voltage characteristics of polyfluorene with dissimilar composition spin coated on ITO. Optik, 2021, 242, 167034.	2.9	5
13	High temperature growth of aluminium doped zirconium oxide via post-sputter oxidation of Al-Zr films with different composition. Journal of Alloys and Compounds, 2020, 813, 152206.	5.5	1
14	Dual-step grown ternary aluminium zirconium oxide and its characteristics for metal-oxide-semiconductor capacitor. Ceramics International, 2020, 46, 10416-10424.	4.8	6
15	Fabrication and characterization of electrospun ZnO nanofibers; antimicrobial assessment. Materials Letters, 2020, 264, 127279.	2.6	24
16	Simultaneous two-step assisted growth of aluminium zirconium oxide from Al-Zr films. Ceramics International, 2020, 46, 297-306.	4.8	4
17	Effects of Post-Deposition Annealing Time in Forming Gas Ambient on Y ₂ O ₃ Films Deposited on Silicon Substrate. Journal of Physics: Conference Series, 2020, 1535, 012031.	0.4	0
18	Growth and Characterization of Ternary Hf _x Ta _y O _z Films via Nitrogen-Infused Wet Oxidation. ACS Omega, 2020, 5, 26347-26356.	3.5	3

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19	Preparation and characterisation of aluminium zirconium oxide for metal-oxide-semiconductor capacitor. International Journal of Energy Research, 2020, 44, 10562-10575.	4.5	2
20	Effect of annealing temperature on physical and electrical properties of solution-processed polycrystalline In ₂ Ga ₂ ZnO ₇ thin film. Journal of Materials Science: Materials in Electronics, 2020, 31, 9705-9718.	2.2	7
21	High-k La _x Ce _y O _z for Passivation of Si Substrate. Journal of Physics: Conference Series, 2020, 1535, 012030.	0.4	0
22	Surface passivation via two-step grown nitrogen infused oxidation derived quaternary Al _x Zr _{1-x} O _y N _z . Materials Letters, 2020, 276, 128175.	2.6	0
23	Effect of microwave time on the structural and luminescence properties of YAG:Ce prepared by microwave solution combustion (MSC) synthesis. Optik, 2020, 212, 164437.	2.9	7
24	Wet oxidation growth of hafnium doped tantalum oxide films with different composition deposited on silicon substrate. Applied Surface Science, 2020, 526, 146722.	6.1	12
25	Passivation of silicon substrate using two-step grown ternary aluminium doped zirconium oxide. Applied Surface Science, 2019, 493, 411-422.	6.1	16
26	Structural, morphological, optical, and gas sensing characteristics of ultraviolet-assisted photoelectrochemical etching derived AlInGaN nano-spikes. Journal of Materials Research and Technology, 2019, 8, 2767-2776.	5.8	9
27	A two-step growth route of ternary aluminium doped zirconium oxide film on silicon. Journal of Alloys and Compounds, 2019, 777, 736-748.	5.5	14
28	Effects of ultraviolet-assisted electrochemical etching current densities on structural and optical characteristics of porous quaternary AlInGaN alloys. Arabian Journal of Chemistry, 2019, 12, 3417-3430.	4.9	13
29	Porous Formation in p-Type Gallium Nitride Films via 50ÂHz Operated Alternating Current-Assisted Photo-Electrochemical Etching in Methanol-Sulfuric Acid Solution. Journal of the Electrochemical Society, 2018, 165, H620-H628.	2.9	11
30	Effects of ammonia ambient annealing on physical and electrical characteristics of rare earth CeO ₂ as passivation film on silicon. Journal of Alloys and Compounds, 2017, 695, 3104-3115.	5.5	27
31	Effects of Calcination on the Crystallography and Nonbiogenic Aragonite Formation of Ark Clam Shell under Ambient Condition. Advances in Materials Science and Engineering, 2016, 2016, 1-8.	1.8	17
32	Porous Quaternary Al _{0.1} In _{0.1} Ga _{0.8} N Film Formation via Photoelectrochemical Etching in HF:C ₂ H ₅ OH Electrolyte. Journal of the American Ceramic Society, 2016, 99, 2395-2401.	3.8	8
33	Surface Alteration of Planar P-Type Gallium Nitride to Porous Structure Using 50 Hz Alternating Current-Assisted Photo-Electrochemical Etching Route. Journal of the Electrochemical Society, 2016, 163, H642-H651.	2.9	10
34	Room temperature hydrogen gas sensing characteristics of porous quaternary AlInGaN film prepared via UV-assisted photo-electrochemical etching. Superlattices and Microstructures, 2016, 95, 65-70.	3.1	2
35	Structural and optical investigation of porous quaternary Al _{0.10} In _{0.10} Ga _{0.80} N films produced via ultraviolet-assisted photo-electrochemical etching in acidic solutions. Journal of Alloys and Compounds, 2016, 662, 32-43.	5.5	9
36	Effects of annealing temperature on optical, morphological, and electrical characteristics of polyfluorene-derivative thin films on ITO glass substrate. Applied Optics, 2016, 55, 1198.	2.1	10

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37	Manganese modified structural and optical properties of zinc soda lime silica glasses. Applied Optics, 2016, 55, 2182.	2.1	13
38	Effects of rapid thermal annealing on structural, chemical, and electrical characteristics of atomic-layer deposited lanthanum doped zirconium dioxide thin film on 4H-SiC substrate. Applied Surface Science, 2016, 365, 296-305.	6.1	8
39	Characterization of Waste Material Derived Willemite-Based Glass-Ceramics Doped with Erbium. Advances in Materials Science and Engineering, 2015, 2015, 1-7.	1.8	17
40	Investigation of Aloe Vera as active layer for development of organic based memory devices. Materials Technology, 2015, 30, A29-A35.	3.0	15
41	An elucidating study on physical and structural properties of 45S5 glass at different sintering temperatures. Journal of Non-Crystalline Solids, 2015, 412, 24-29.	3.1	16
42	Alteration of structural and optical properties in quaternary Al _{0.1} In _{0.1} Ga _{0.8} N films using ultraviolet assisted photo-electrochemical etching route. Journal of Alloys and Compounds, 2015, 649, 337-347.	5.5	22
43	Investigation on structural and optical properties of SLS [®] ZnO glasses prepared using a conventional melt quenching technique. Journal of Materials Science: Materials in Electronics, 2015, 26, 3722-3729.	2.2	35
44	Effects of CNTs content and milling time on mechanical behavior of MWCNT-reinforced aluminum nanocomposites. Materials Chemistry and Physics, 2015, 166, 160-166.	4.0	56
45	Characterization of Aging Behavior of AA6061 Aluminum Alloy Through Destructive and Ultrasonic Non-destructive Testing Techniques. Transactions of the Indian Institute of Metals, 2015, 68, 561-569.	1.5	4
46	Effect of Sintering Temperature on Structural and Morphological Properties of Europium (III) Oxide Doped Willemite. Journal of Spectroscopy, 2014, 2014, 1-8.	1.3	34
47	Influence of post-deposition annealing time on oxygen gas sensing behaviour of Al _{0.50} Ce _{0.50} O _{1.75} /Si metal-oxide-semiconductor capacitor. Materials Research Innovations, 2014, 18, S6-490-S6-494.	2.3	2
48	Oxygen vacancy formation and annihilation in lanthanum cerium oxide as a metal reactive oxide on 4H-silicon carbide. Physical Chemistry Chemical Physics, 2014, 16, 7015.	2.8	30
49	Ultralow Voltage Operation of $\{m \text{ Al}\} / \{m \text{ La}\}_{x} \{m \text{ Ce}\}_{1-x} \{m \text{ O}\}_{z} / \{m \text{ 4H-SiC}\}$ for Oxygen Sensing. IEEE Electron Device Letters, 2013, 34, 1430-1432.	3.9	3
50	Effects of post-deposition annealing temperature on metal-organic decomposed lanthanum cerium oxide film as metal reactive oxide layer on 4H-SiC. Materials Chemistry and Physics, 2013, 140, 622-633.	4.0	17
51	Study of molar ratio on the characteristics of metal [®] organic decomposed La _x Ce _{1-x} O _z film as a metal reactive oxide on Si substrate. Journal of Alloys and Compounds, 2013, 581, 793-800.	5.5	19
52	Structural and Chemical Studies of Metal [®] Organic Decomposed La _x Ce _y O _z Thin Film as a Catalytic Oxide on 4H-SiC as a Function of Postdeposition Annealing Time. Journal of Physical Chemistry C, 2013, 117, 14014-14024.	3.1	22
53	Effects of Post-Deposition Annealing Temperature on Band Alignment and Electrical Characteristics of Lanthanum Cerium Oxide on 4H-SiC. Materials Research Society Symposia Proceedings, 2012, 1433, 7.	0.1	5
54	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film. , 2012, , .		0

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55	Metal-oxide-semiconductor characteristics of lanthanum cerium oxide film on Si. Applied Physics A: Materials Science and Processing, 2012, 107, 459-467.	2.3	21
56	Influence of post-deposition annealing in oxygen ambient on metal-organic decomposed CeO ₂ film spin coated on 4H-SiC. Journal of Materials Science: Materials in Electronics, 2012, 23, 257-266.	2.2	21
57	Physical and electrical characteristics of metal-organic decomposed CeO ₂ gate spin-coated on 4H-SiC. Applied Physics A: Materials Science and Processing, 2011, 103, 1067-1075.	2.3	26
58	Comparison of metal-organic decomposed (MOD) cerium oxide (CeO ₂) gate deposited on GaN and SiC substrates. Journal of Crystal Growth, 2011, 326, 2-8.	1.5	37
59	Effects of post-deposition annealing temperature and time on physical properties of metal-organic decomposed lanthanum cerium oxide thin film. Thin Solid Films, 2011, 519, 5139-5145.	1.8	24
60	Influence of post-deposition annealing on metal-organic decomposed lanthanum cerium oxide film. , 2011, , .		7
61	Electrical Properties of Pulsed Laser Deposited Y ₂ O ₃ Gate Oxide on 4H-SiC. Electrochemical and Solid-State Letters, 2010, 13, H396.	2.2	33
62	Effects of Postdeposition Annealing in Argon Ambient on Metallorganic Decomposed CeO ₂ Gate Spin Coated on Silicon. Journal of the Electrochemical Society, 2010, 157, H6.	2.9	61
63	Physical characterization of post-deposition annealed metal-organic decomposed cerium oxide film spin-coated on 4H-silicon carbide. Journal of Alloys and Compounds, 2010, 497, 195-200.	5.5	26
64	Effects of Post-Deposition Annealing on CeO ₂ Gate Prepared by Metal-Organic Decomposition (MOD) Method on 4H-SiC. Materials Science Forum, 0, 645-648, 837-840.	0.3	20
65	Effects of Post-Deposition Annealing Time on Metal-Organic Decomposed Lanthanum Cerium Oxide Film Spin-Coated on Si Substrate. Advanced Materials Research, 0, 1024, 364-367.	0.3	1